

# PTF 10154

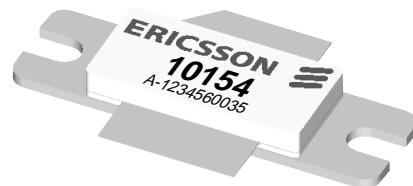
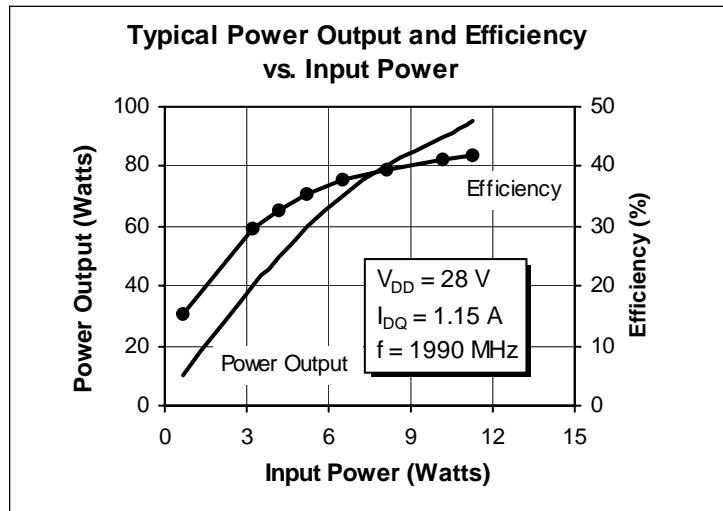
## 85 Watts, 1.93–1.99 GHz

### GOLDMOS® Field Effect Transistor

#### Description

The PTF 10154 is an internally matched 85-watt GOLDMOS FET intended for CDMA and TDMA applications from 1.93 to 1.99 GHz. This device operates at 43% efficiency with 11 dB gain. Nitride surface passivation and full gold metallization ensure excellent device lifetime and reliability.

- **INTERNALLY MATCHED**
- Guaranteed Performance at 1.93, 1.99 GHz, 28 V
  - Output Power = 85 Watts Min
  - Power Gain = 11 dB Typ
- Full Gold Metallization
- Silicon Nitride Passivated
- Back Side Common Source
- Excellent Thermal Stability
- 100% Lot Traceability



Package 20248

#### RF Specifications (100% Tested)

Characteristic	Symbol	Min	Typ	Max	Units
<b>Gain</b> (V <sub>DD</sub> = 28 V, P <sub>OUT</sub> = 10 W, I <sub>DQ</sub> = 1.15 A, f = 1.96, 1.99 GHz)	G <sub>ps</sub>	10.0	11	—	dB
<b>Power Output at 1 dB Compression</b> (V <sub>DD</sub> = 28 V, I <sub>DQ</sub> = 1.15 A, f = 1.99 GHz)	P-1dB	85	—	—	Watts
<b>Drain Efficiency</b> (V <sub>DD</sub> = 28 V, P <sub>OUT</sub> = 90 W, I <sub>DQ</sub> = 1.15 A, f = 1.99 GHz)	η <sub>D</sub>	—	43	—	%
<b>Load Mismatch Tolerance</b> (V <sub>DD</sub> = 28 V, P <sub>OUT</sub> = 90 W, I <sub>DQ</sub> = 1.15 A, f = 1.99 GHz —all phase angles at frequency of test)	Ψ	—	—	10:1	—

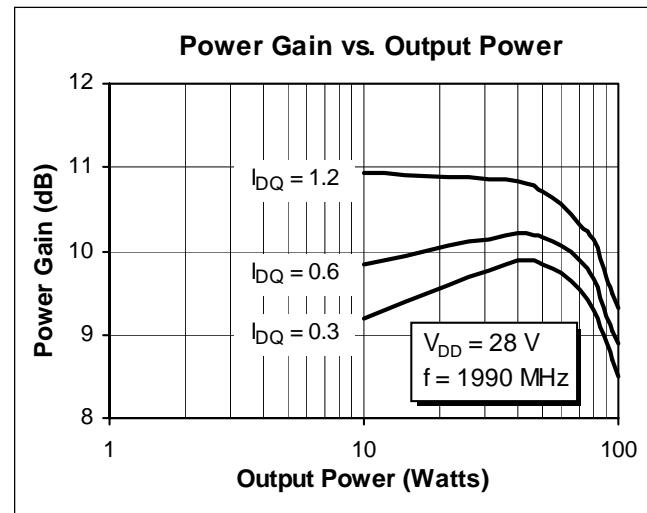
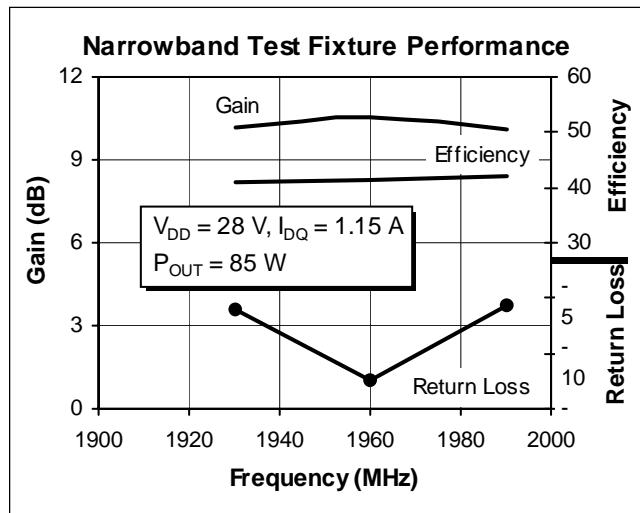
All published data at T<sub>CASE</sub> = 25°C unless otherwise indicated.

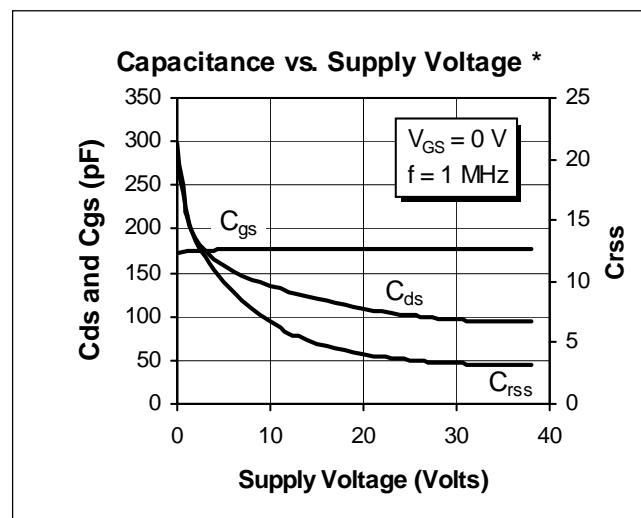
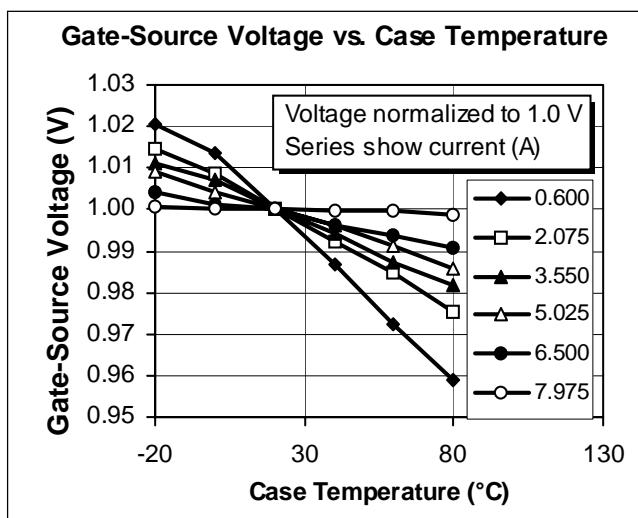
**Electrical Characteristics** (100% Tested)

Characteristic	Conditions	Symbol	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}$ , $I_D = 100 \text{ mA}$	$V_{(BR)DSS}$	65	—	—	Volts
Zero Gate Voltage Drain Current	$V_{DS} = 28 \text{ V}$ , $V_{GS} = 0 \text{ V}$	$I_{DSS}$	—	—	5.0	mA
Gate Threshold Voltage	$V_{DS} = 10 \text{ V}$ , $I_D = 150 \text{ mA}$	$V_{GS(\text{th})}$	3.0	—	5.0	Volts
Forward Transconductance	$V_{DS} = 10 \text{ V}$ , $I_D = 2 \text{ A}$	$g_{fs}$	—	1.0	—	Siemens

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	65	Vdc
Gate-Source Voltage	$V_{GS}$	$\pm 20$	Vdc
Operating Junction Temperature	$T_J$	200	°C
Total Device Dissipation at Above 25°C derate by	$P_D$	365	Watts
		2.08	W/°C
Storage Temperature Range	$T_{STG}$	-40 to +150	°C
Thermal Resistance ( $T_{CASE} = 70^\circ\text{C}$ )	$R_{\theta JC}$	0.48	°C/W

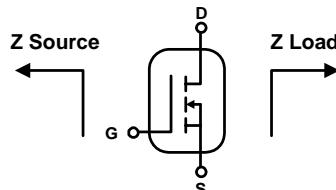
**Typical Performance**



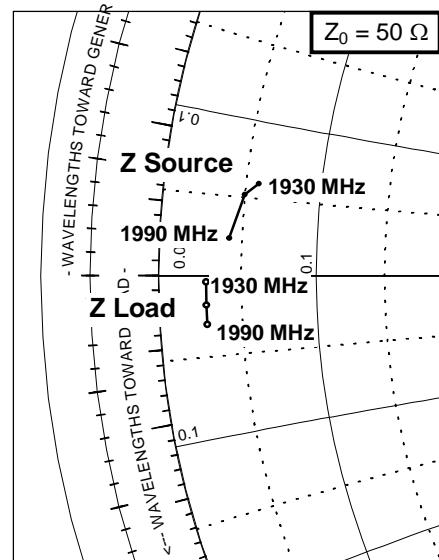
\* This part is internally matched. Measurements of the finished product will not yield these results.

## Impedance Data

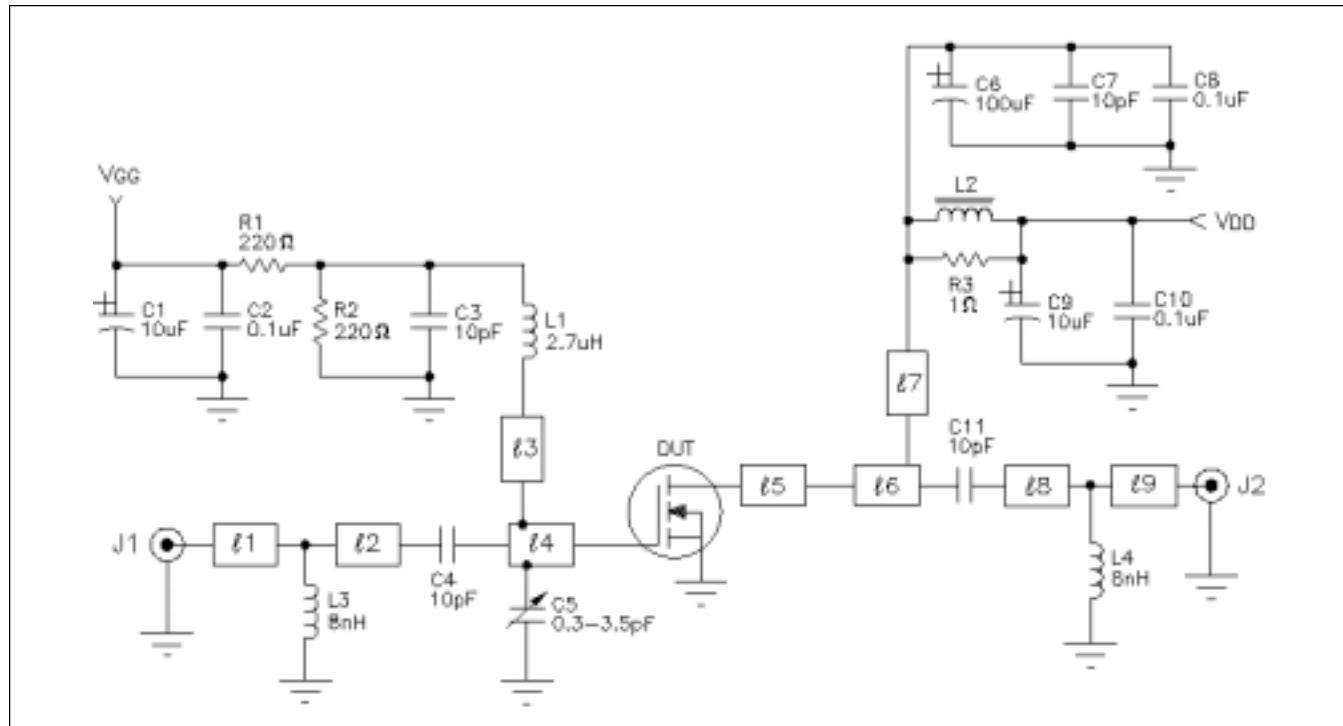
$V_{DD} = 28 \text{ V}$ ,  $P_{OUT} = 85 \text{ W}$ ,  $I_{DQ} = 1.15 \text{ A}$



Frequency	<b>Z Source</b> $\Omega$		<b>Z Load</b> $\Omega$	
GHz	R	jX	R	jX
1930	2.9	3.0	1.4	-0.2
1960	2.5	2.6	1.4	-0.9
1990	2.1	1.2	1.4	-1.5

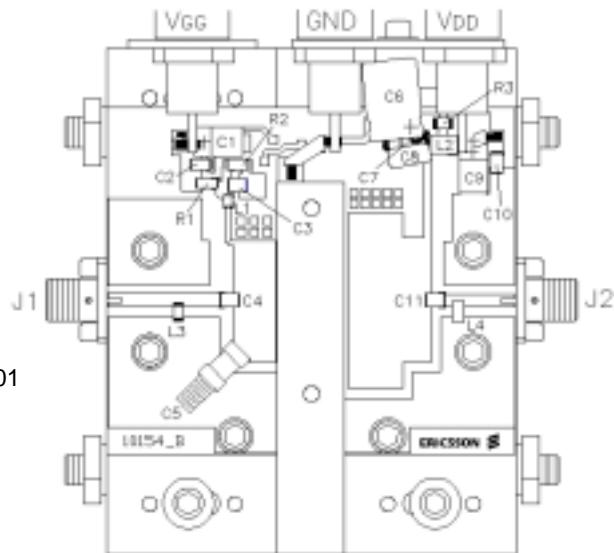


## Test Circuit

Test Circuit Block Diagram for  $f = 1.93\text{--}1.99 \text{ GHz}$ 

Q1 PTF 10154 LDMOS RF Transistor

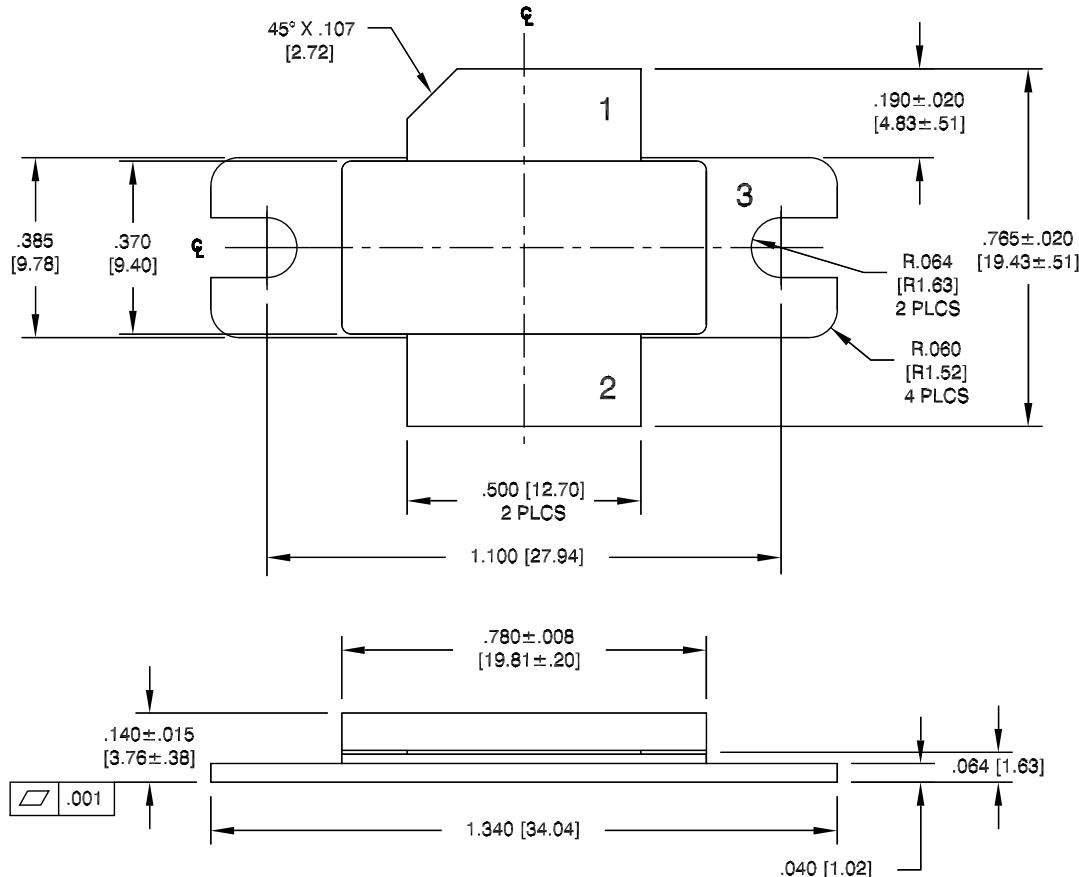
1.96 GHz	IPM (OHMS)
$\ell_1$	0.105 $\lambda$ 1.96 GHz Microstrip 50 $\Omega$
$\ell_2$	0.119 $\lambda$ 1.96 GHz Microstrip 50 $\Omega$
$\ell_3$	0.073 $\lambda$ 1.96 GHz Microstrip 76.64 $\Omega$
$\ell_4$	0.094 $\lambda$ 1.96 GHz Microstrip 9.73 $\Omega$
$\ell_5$	0.126 $\lambda$ 1.96 GHz Microstrip 6.67 $\Omega$
$\ell_6$	0.614 $\lambda$ 1.96 GHz Microstrip 9.62 $\Omega$
$\ell_7$	0.170 $\lambda$ 1.96 GHz Microstrip 64.30 $\Omega$
$\ell_8$	0.050 $\lambda$ 1.96 GHz Microstrip 50 $\Omega$
$\ell_9$	0.073 $\lambda$ 1.96 GHz Microstrip 50 $\Omega$
C1, C9	Capacitor, 10 $\mu\text{F}$ Digi-Key pcs 6106
C2, C10	Capacitor, 0.1 $\mu\text{F}$ , 50V Digi-Key PCC103BCT
C3, C4, C7, C11	Capacitor, 10pF ATC 100 b
C5	Capacitor, variable 0.3–3.5pF JACO johanson 5801
C6	Capacitor, 100 $\mu\text{F}$ , 50V Digi-Key P5182-ND
C8	Capacitor, 0.1 $\mu\text{F}$ , 50V Digi-Key P4525-ND
J1, J2	Connector, SMA female, panel mount 1301-rpm 513 412/53
L1	Chip inductor, 2.7 $\mu\text{H}$
L2	Ferrite, 6mm phillips 53/3/4.6-452
L3, L4	Inductor, 8nH coilcraft 0805CS-080 jbc
R1, R2	Resistor, 220 ohm Digi-Key 220 qbk
R3	Resistor, 1 ohm DIGI-KEY 1.0 qbk
Circuit Board	0.050", 2 OZ Copper rogers corporation, TMM6



Parts Layout (not to scale)

## Package Mechanical Specifications

## Package 20248



Unless otherwise specified  
all tolerance  $\pm 0.005"$  [0.13mm]

Pins: 1. Drain 2. Gate 3. Source  
Lead Thickness: 0.004 +0.002/-0.001"  
[0.10 +.05/-0.03mm]

Primary Dimensions are in inches, alternate dimensions are mm.